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## 1 Block diagram





## Typical power

Part number	230 V <sub>AC</sub>		85-265 V <sub>AC</sub>		
Fart number	Adapter <sup>(1)</sup>	Open frame <sup>(2)</sup>	Adapter <sup>(1)</sup>	Open frame <sup>(2)</sup>	
VIPER16	9 W	10 W	5 W	6 W	

1. Typical continuous power in non ventilated enclosed adapter measured at 50 °C ambient.

2. Maximum practical continuous power in an open frame design at 50  $^\circ\text{C}$  ambient, with adequate heat sinking.

2



## 3 Pin settings



Figure 3. Connection diagram (top view)

Note:

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The copper area for heat dissipation has to be designed under the DRAIN pins.

Pin	N.	Name	Function		
DIP-7	SO16	Name	Function		
1	1-2	GND	Connected to the source of the internal power MOSFET and controller ground reference.		
-	4	N.A.	Not available for user. This pin is mechanically connected to the controller die pad of the frame. In order to improve the noise immunity, is highly recommended connect it to GND (pin 1-2).		
2	5	VDD	Supply voltage of the control section. This pin provides the charging current of the external capacitor.		
3	6	LIM	This pin allows setting the drain current limitation to a lower value respect to $I_{Dlim}$ , which is the default one. The limit can be reduced by connecting an external resistor between this pin and GND. In case of high electrical noise, a capacitor could be connected between this pin and GND, the capacitor value must be lower than 470 nF in order to not impact the functionality of the pin. The pin can be left open if default drain current limitation, $I_{Dlim}$ , is used.		
4	7	FB	Inverting input of the internal trans conductance error amplifier. Connecting the converter output to this pin through a single resistor results in an output voltage equal to the error amplifier reference voltage (see $V_{FB\_REF}$ on <i>Table 8</i> ). An external resistors divider is required for higher output voltages.		

#### Table 3. Pin description



Pin	Pin N.		E-marking.			
DIP-7	SO16	Name	Function			
5	8	COMP	Output of the internal trans conductance error amplifier. The compensation network have to be placed between this pin and GND to achieve stability and good dynamic performance of the voltage control loop. The pin is used also to directly control the PWM with an optocoupler. The linear voltage range extends from $V_{COMPL}$ to $V_{COMPH}$ ( <i>Table 8</i> ).			
7,8	13-16	DRAIN	High voltage drain pin. The built-in high voltage switched start-up bias current is drawn from this pin too. Pins connected to the metal frame to facilitate heat dissipation.			



## 4 Electrical data

### 4.1 Maximum ratings

	Pin	7) Parameter -		alue	11
Symbol (	(DIP-7)			Max	Unit
V <sub>DRAIN</sub>	7, 8	Drain-to-source (ground) voltage		800	V
E <sub>AV</sub>	7, 8	Repetitive avalanche energy (limited by $T_J = 150 \text{ °C}$ )		2	mJ
I <sub>AR</sub>	7, 8	Repetitive avalanche current (limited by $T_J = 150 \text{ °C}$ )		1	А
I <sub>DRAIN</sub>	7, 8	Pulse drain current (limited by $T_J = 150 \text{ °C}$ )		2.5	А
V <sub>COMP</sub>	5	Input pin voltage	-0.3	3.5	V
V <sub>FB</sub>	4	Input pin voltage	-0.3	4.8	V
V <sub>LIM</sub>	3	Input pin voltage	-0.3	2.4	V
V <sub>DD</sub>	2	Supply voltage	-0.3	Self limited	V
I <sub>DD</sub>	2	Input current		20	mA
р		Power dissipation at T <sub>A</sub> < 40 °C (DIP-7)		1	W
P <sub>TOT</sub>		Power dissipation at T <sub>A</sub> < 60 °C (SO16N)		1	W
TJ		Operating junction temperature range	-40	150	°C
T <sub>STG</sub>		Storage temperature	-55	150	°C
ESD <sub>(HBM)</sub>	1 to 8	Human body model		4	kV
ESD <sub>(CDM)</sub>	1 to 8	Charge device model		1.5	kV

#### Table 4. Absolute maximum ratings

### 4.2 Thermal data

#### Table 5. Thermal data

Symbol	Parameter	Max value SO16N	Max value DIP-7	Unit	
R <sub>thJP</sub>	Thermal resistance junction pin (Dissipated power = 1 W)	35	40	°C/W	
R <sub>thJA</sub>	Thermal resistance junction ambient (Dissipated power = 1 W)	90	110	°C/W	
R <sub>thJA</sub>	Thermal resistance junction ambient <sup>(1)</sup> (Dissipated power = 1 W)	80	90	°C/W	

1. When mounted on a standard single side FR4 board with 100  $\text{mm}^2$  (0.155 sq in) of Cu (35  $\mu\text{m}$  thick)



### 4.3 Electrical characteristics

(T<sub>J</sub> = -25 to 125 °C, V<sub>DD</sub> = 14 V  $^{(a)}$ ; unless otherwise specified)

Symbol	Parameter	Test condition	Min	Тур	Max	Unit
V <sub>BVDSS</sub>	Break-down voltage	I <sub>DRAIN</sub> = 1 mA, V <sub>COMP</sub> = GND, T <sub>J</sub> = 25 °C	800			V
Passa	Drain-source on state resistance	I <sub>DRAIN</sub> = 0.2 A, T <sub>J</sub> = 25 °C		20	24	Ω
R <sub>DS(on)</sub>		I <sub>DRAIN</sub> = 0.2 A, T <sub>J</sub> = 125 °C		40	48	Ω
C <sub>OSS</sub>	Effective (energy related) output capacitance	V <sub>DRAIN</sub> = 0 to 640 V		10		pF
I	OFF state drain current	V <sub>DRAIN</sub> = 640 V V <sub>FB</sub> = GND			60	μA
IOFF		V <sub>DRAIN</sub> = 800 V V <sub>FB</sub> = GND			75	μA

#### Table 6. Power section

Table	7	Sur	nlv	section
Table		Jup	piy	Section

Table 7. Supply Section								
Symbol	DI Parameter Test condition				Max	Unit		
Voltage								
V <sub>DRAIN_START</sub>	Drain-source start voltage		40	50	60	V		
I <sub>DDch1</sub>	Start up charging current	V <sub>DRAIN</sub> = 100 V to 640 V, V <sub>DD</sub> = 4 V	-0.6		-1.8	mA		
I <sub>DDch2</sub>	Charging current during operation	$V_{DRAIN} = 100 V \text{ to } 640 V,$ $V_{DD} = 9 V \text{ falling edge}$	-7		-14	mA		
V <sub>DD</sub>	Operating voltage range		11.5		23.5	V		
V <sub>DDclamp</sub>	V <sub>DD</sub> clamp voltage	I <sub>DD</sub> = 15 mA	23.5			V		
V <sub>DDon</sub>	V <sub>DD</sub> start up threshold		12	13	14	V		
V <sub>DDCSon</sub>	VDD on internal high voltage current generator threshold		9.5	10.5	11.5	V		
V <sub>DDoff</sub>	$V_{DD}$ under voltage shutdown threshold		7	8	9	V		

a. Adjust  $V_{\text{DD}}$  above  $V_{\text{DDon}}$  start-up threshold before setting to 14 V





Symbol	Parameter	Test condition	Min	Тур	Max	Unit
Current						
I <sub>DD0</sub>	Operating supply current, not switching	$F_{OSC} = 0 \text{ kHz}, V_{COMP} = GND$			0.6	mA
		V <sub>DRAIN</sub> = 120 V, F <sub>SW</sub> = 60 kHz			1.3	mA
I <sub>DD1</sub>	Operating supply current, switching	V <sub>DRAIN</sub> = 120 V, F <sub>SW</sub> = 115 kHz			1.5	mA
I <sub>DDoff</sub>	Operating supply current with $V_{DD} < V_{DDoff}$	V <sub>DD</sub> < V <sub>DDoff</sub>			0.35	mA
I <sub>DDol</sub>	Open loop failure current threshold	$V_{DD} = V_{DDclamp}$ $V_{COMP} = 3.3 V,$	4			mA

#### Table 7. Supply section (continued)

#### Table 8. Controller section

Symbol	Parameter	Test condition	Min	Тур	Max	Unit
Error amplifi	er		1		1	
V <sub>REF_FB</sub>	FB reference voltage		3.2	3.3	3.4	V
I <sub>FB_PULL UP</sub>	Current pull up			-1		μΑ
G <sub>M</sub>	Trans conductance			2		mA/V
Current setti	ng (LIM) pin					
V <sub>LIM_LOW</sub>	Low level clamp voltage	I <sub>LIM</sub> = -100 μA		0.5		V
Compensatio	on (COMP) pin					
V <sub>COMPH</sub>	Upper saturation limit	T <sub>J</sub> = 25 °C		3		V
V <sub>COMPL</sub>	Burst mode threshold	T <sub>J</sub> = 25 °C	1	1.1	1.2	V
V <sub>COMPL_HYS</sub>	Burst mode hysteresis	T <sub>J</sub> = 25 °C		40		mV
H <sub>COMP</sub>	ΔV <sub>COMP</sub> / ΔI <sub>DRAIN</sub>		4		9	V/A
R <sub>COMP(DYN)</sub>	Dynamic resistance	V <sub>FB</sub> = GND		15		kΩ
	Source / sink current	V <sub>FB</sub> > 100 mV		150		μA
I <sub>COMP</sub>	Max source current	$V_{COMP}$ = GND, $V_{FB}$ = GND		220		μΑ
Current limit	ation					
I <sub>Dlim</sub>	Drain current limitation	$I_{LIM} = -10 \ \mu\text{A}, \ V_{COMP} = 3.3 \ \text{V}, \\ T_{J} = 25 \ ^{\circ}\text{C}$	0.38	0.4	0.42	А
t <sub>SS</sub>	Soft-start time			8.5		ms
T <sub>ON_MIN</sub>	Minimum turn ON time		220		450	ns
I <sub>Dlim_bm</sub>	Burst mode current limitation	V <sub>COMP</sub> = V <sub>COMPL</sub>		85		mA
Overload						
t <sub>OVL</sub>	Overload time			50		ms
t <sub>restart</sub>	Restart time after fault			1		S



Symbol	Parameter	Test condition	Min	Тур	Max	Unit
Oscillator s	ection				•	
	Switching frequency	VIPer16L	54	60	66	kHz
F <sub>OSC</sub>	Switching frequency	VIPer16H	103	115	127	kHz
F <sub>D</sub>	Modulation depth	F <sub>OSC</sub> = 60 kHz		±4		kHz
		F <sub>OSC</sub> = 115 kHz		±8		kHz
F <sub>M</sub>	Modulation frequency			230		Hz
D <sub>MAX</sub>	Maximum duty cycle		70		80	%
Thermal shu	utdown					
T <sub>SD</sub>	Thermal shutdown temperature <sup>(1)</sup>		150	160		°C
T <sub>HYST</sub>	Thermal shutdown hysteresis <sup>(1)</sup>			30		°C

 Table 8. Controller section (continued)

1. Specification assured by design, characterization and statistical correlation.

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## **5** Typical electrical characteristics



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Figure 12. Operating supply current (switching) vs  $T_{\rm J}$ 





Figure 14. Power MOSFET on-resistance vs  $T_J$  Figure 15. Power MOSFET break down voltage



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Figure 16. Thermal shutdown



# 6 Typical circuit



Figure 18. Buck boost converter







Figure 19. Flyback converter (primary regulation)

Figure 20. Flyback converter (non isolated)





#### 7 Power section

The power section is implemented with an n-channel power MOSFET with a breakdown voltage of 800 V min. and a typical  $R_{DS(on)}$  of 20  $\Omega$ . It includes a SenseFET structure to allow a virtually lossless current sensing and the thermal sensor.

The gate driver of the power MOSFET is designed to supply a controlled gate current during both turn-ON and turn-OFF in order to minimize common mode EMI. During UVLO conditions, an internal pull-down circuit holds the gate low in order to ensure that the power MOSFET cannot be turned ON accidentally.

#### 8 High voltage current generator

The high voltage current generator is supplied by the DRAIN pin. At the first start up of the converter it is enabled when the voltage across the input bulk capacitor reaches the  $V_{DRAIN\_START}$  threshold, sourcing a  $I_{DDch1}$  current (see *Table 7 on page 8*); as the  $V_{DD}$  voltage reaches the  $V_{DDon}$  threshold, the power section starts switching and the high voltage current generator is turned OFF. The VIPer16 is powered by the energy stored in the  $V_{DD}$  capacitor.

In steady state condition, if the self biasing function is used, the high voltage current generator is activated between  $V_{DDCSon}$  and  $V_{DDon}$  (see *Table 7 on page 8*), delivering  $I_{DDch2}$ , see *Table 7 on page 8* to the  $V_{DD}$  capacitor during the MOSFET off time (see *Figure 21 on page 16*).

The device can also be supplied through the auxiliary winding; in this case the high voltage current source is disabled during steady-state operation, provided that VDD is above  $V_{\text{DDCSon}}$ .

At converter power-down, the  $V_{DD}$  voltage drops and the converter activity stops as it falls below  $V_{DDoff}$  threshold (see *Table 7 on page 8*).



Figure 21. Power on and power off

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#### 9 Oscillator

The switching frequency is internally fixed at 60 kHz (part number VIPER16LN or LD) or 115 kHz (part number VIPER16HN or HD).

In both cases the switching frequency is modulated by approximately  $\pm 4$  kHz (60 kHz version) or  $\pm 8$  kHz (115 kHz version) at 230 Hz (typical) rate, so that the resulting spread-spectrum action distributes the energy of each harmonic of the switching frequency over a number of sideband harmonics having the same energy on the whole but smaller amplitudes.

### 10 Soft start-up

During the converters' start-up phase, the soft-start function progressively increases the cycle-by-cycle drain current limit, up to the default value  $I_{Dlim}$ . By this way the drain current is further limited and the output voltage is progressively increased reducing the stress on the secondary diode. The soft-start time is internally fixed to  $t_{SS}$ , see typical value on *Table 8 on page 9*, and the function is activated for any attempt of converter start-up and after a fault event.

This function helps prevent transformers' saturation during start-up and short-circuit.

### 11 Adjustable current limit set point

The VIPer16 includes a current mode PWM controller: cycle by cycle the drain current is sensed through the integrated resistor R<sub>SENSE</sub> and the voltage is applied to the non inverting input of the PWM comparator, see *Figure 2 on page 4*. As soon as the sensed voltage is equal to the voltage derived from the COMP pin, the power MOSFET is switched OFF.

In parallel with the PWM operations, the comparator OCP, see *Figure 2 on page 4*, checks the level of the drain current and switch OFF the power MOSFET in case the current is higher than the threshold I<sub>Dlim</sub>, see *Table 8 on page 9*.

The level of the drain current limit,  $I_{Dlim}$ , can be reduced depending from the sunk current from the pin LIM. The resistor  $R_{LIM}$ , between LIM and GND pins, fixes the current sunk and than the level of the current limit,  $I_{Dlim}$ , see *Figure 13 on page 12*.

When the LIM pin is left open or if the R<sub>LIM</sub> has an high value (i.e. > 80 k $\Omega$ ) the current limit is fixed to its default value, I<sub>Dlim</sub>, as reported on *Table 8 on page 9*.



### 12 FB pin and COMP pin

The device can be used both in non-isolated and in isolated topology. In case of nonisolated topology, the feedback signal from the output voltage is applied directly to the FB pin as inverting input of the internal error amplifier having the reference voltage, V<sub>REF\_FB</sub>, see the *Table 8 on page 9*.

The output of the error amplifier sources and sinks the current,  $I_{COMP}$  respectively to and from the compensation network connected on the COMP pin. This signal is then compared, in the PWM comparator, with the signal coming from the SenseFET; the power MOSFET is switched off when the two values are the same on cycle by cycle basis. See the *Figure 2 on page 4* and the *Figure 22 on page 18*.

When the power supply output voltage is equal to the error amplifier reference voltage,  $V_{REF\_FB}$ , a single resistor has to be connected from the output to the FB pin. For higher output voltages the external resistor divider is needed. If the voltage on FB pin is accidentally left floating, an internal pull-up protects the controller.

The output of the error amplifier is externally accessible through the COMP pin and it's used for the loop compensation: usually an RC network.

As reported on *Figure 22 on page 18*, in case of isolated power supply, the internal error amplifier has to be disabled (FB pin shorted to GND). In this case an internal resistor is connected between an internal reference voltage and the COMP pin, see the *Figure 22 on page 18*. The current loop has to be closed on the COMP pin through the opto-transistor in parallel with the compensation network. The V<sub>COMP</sub> dynamics ranges is between V<sub>COMPL</sub> and V<sub>COMPH</sub> as reported on *Figure 23 on page 19*.

When the voltage  $V_{COMP}$  drops below the voltage threshold  $V_{COMPL}$ , the converter enters burst mode, see Section 13 on page 19.

When the voltage  $V_{COMP}$  rises above the  $V_{COMPH}$  threshold, the peak drain current will reach its limit, as well as the deliverable output power.



#### Figure 22. Feedback circuit

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Figure 23. COMP pin voltage versus IDRAIN

### 13 Burst mode

When the voltage  $V_{COMP}$  drops below the threshold,  $V_{COMPL}$ , the power MOSFET is kept in OFF state and the consumption is reduced to  $I_{DD0}$  current, as reported on *Table 7 on page 8*. As reaction at the energy delivery stop, the  $V_{COMP}$  voltage increases and as soon as it exceeds the threshold  $V_{COMPL} + V_{COMPL_HYS}$ , the converter starts switching again with consumption level equal to  $I_{DD1}$  current. This ON-OFF operation mode, referred to as "burst mode" and reported on *Figure 24 on page 19*, reduces the average frequency, which can go down even to a few hundreds hertz, thus minimizing all frequency-related losses and making it easier to comply with energy saving regulations. During the burst mode, the drain current limit is reduced to the value  $I_{Dlim_bm}$  (reported on *Table 8 on page 9*) in order to avoid the audible noise issue.



Figure 24. Load-dependent operating modes: timing diagrams



#### 14 Automatic auto restart after overload or short-circuit

The overload protection is implemented in automatic way using the integrated up-down counter. Every cycle, it is incremented or decremented depending if the current logic detects the limit condition or not. The limit condition is the peak drain current,  $I_{Dlim}$ , reported on *Table 8 on page 9* or the one set by the user through the R<sub>LIM</sub> resistor, as reported in *Figure 13 on page 12*. After the reset of the counter, if the peak drain current is continuously equal to the level  $I_{Dlim}$ , the counter will be incremented till the fixed time,  $t_{OVL}$ , after that will be disabled the power MOSFET switch ON. It will be activated again, through the soft start, after the  $t_{RESTART}$  time, see the *Figure 25* and *Figure 26 on page 20* and the mentioned time values on *Table 8 on page 9*.

In case of overload or short-circuit event, the power MOSFET switching will be stopped after a time that depends from the counter and that can be as maximum equal to t<sub>OVL</sub>. The protection will occur in the same way until the overload condition is removed, see *Figure 25* and *Figure 26 on page 20*. This protection ensures restart attempts of the converter with low repetition rate, so that it works safely with extremely low power throughput and avoiding the IC overheating in case of repeated overload events. If the overload is removed before the protection tripping, the counter will be decremented cycle by cycle down to zero and the IC will not be stopped.



Figure 25. Timing diagram: OLP sequence (IC externally biased)



Figure 26. Timing diagram: OLP sequence (IC internally biased)

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### 15 Open loop failure protection

In case the power supply is built in fly-back topology and the VIPer16 is supplied by an auxiliary winding, as shown in *Figure 27 on page 21* and *Figure 28 on page 22*, the converter is protected against feedback loop failure or accidental disconnections of the winding.

The following description is applicable for the schematics of *Figure 27 on page 21* and *Figure 28 on page 22*, respectively the non-isolated fly-back and the isolated fly-back.

If  $R_H$  is opened or  $R_L$  is shorted, the VIPer16 works at its drain current limitation. The output voltage,  $V_{OUT}$ , will increase and so the auxiliary voltage,  $V_{AUX}$ , which is coupled with the output through the secondary-to-auxiliary turns ratio.

As the auxiliary voltage increases up to the internal  $V_{DD}$  active clamp,  $V_{DDclamp}$  (the value is reported on *Table 8 on page 9*) and the clamp current injected on VDD pin exceeds the latch threshold,  $I_{DDol}$  (the value is reported on *Table 8 on page 9*), a fault signal is internally generated.

In order to distinguish an actual malfunction from a bad auxiliary winding design, both the above conditions (drain current equal to the drain current limitation and current higher than  $I_{DDol}$  through VDD clamp) have to be verified to reveal the fault.

If  $R_L$  is opened or  $R_H$  is shorted, the output voltage,  $V_{OUT}$ , will be clamped to the reference voltage  $V_{REF\_FB}$  (in case of non isolated fly-back) or to the external TL voltage reference (in case of isolated fly-back).









Figure 28. FB pin connection for isolated fly-back

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### 16 Layout guidelines and design recommendations

A proper printed circuit board layout is essential for correct operation of any switch-mode converter and this is true for the VIPer16 as well. Also some trick can be used to make the design rugged versus external influences.

Careful component placing, correct traces routing, appropriate traces widths and compliance with isolation distances are the major issues.

The main reasons to have a proper PCB routing are:

- Provide a noise free path for the signal ground and for the internal references, ensuring good immunity against external noises and switching noises
- Minimize the pulsed loops (both primary and secondary) to reduce the electromagnetic interferences, both radiated and conducted and passing more easily the EMC regulations.

The below list can be used as guideline when designing a SMPS using VIPer16.

- Signal ground routing should be routed separately from power ground and, in general, from any pulsed high current loop;
- Connect all the signal ground traces to the power ground, using a single "star point", placed close to the IC GND pin;
- With flyback topologies, when the auxiliary winding is used, it is suggested to connect the VDD capacitor on the auxiliary return and then to the main GND using a single track;
- The compensation network should be connected as close as possible to the COMP pin, maintaining the trace for the GND as short as possible;
- A small bypass capacitor (a few hundreds pF up to 0.1 µF) to GND might be useful to get a clean bias voltage for the signal part of the IC and protect the IC itself during EFT/ESD tests. A low ESL ceramic capacitor should be used, placed as close as possible to the VDD pin;
- When using SO16 package it is recommended to connect the pin 4 to GND pin, using a signal track, in order to improve the noise immunity. This is highly recommended in case of high nosily environment;
- An optional capacitor can be connected on the LIM pin in order to improve the IC noise immunity. It is strongly recommended to don't exceed 470nF.
- The IC thermal dissipation takes place through the drain pins. An adequate heat sink copper area has to be designed under the drain pins to improve the thermal dissipation;
- It is not recommended to place large copper areas on the GND pins.
- Minimize the area of the pulsed loops (primary, RCD and secondary loops), in order to reduce its parasitic self- inductance and the radiated electromagnetic field: this will greatly reduce the electromagnetic interferences produced by the power supply during the switching.





Figure 29. Suggested routing for converter: flyback case

#### Figure 30. Suggested routing for converter: buck case



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VIPER16

## 17 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: www.st.com. ECOPACK<sup>®</sup> is an ST trademark.



Figure 31. DIP-7 package dimensions



Dim	mm			
Dim.	Тур	Min	Max	
А			5,33	
A1		0,38		
A2	3,30	2,92	4,95	
b	0,46	0,36	0,56	
b2	1,52	1,14	1,78	
С	0,25	0,20	0,36	
D	9,27	9,02	10,16	
E	7,87	7,62	8,26	
E1	6,35	6,10	7,11	
е	2,54			
eA	7,62			
eB			10,92	
L	3,30	2,92	3,81	
M <sup>(6)(8)</sup>	2,508			
Ν	0,50	0,40	0,60	
N1			0,60	
O <sup>(7)(8)</sup>	0,548			

1- The leads size is comprehensive of the thickness of the leads finishing material.

2- Dimensions do not include mold protrusion, not to exceed 0,25 mm in total (both side).

3- Package outline exclusive of metal burrs dimensions.

4- Datum plane "H" coincident with the bottom of lead, where lead exits body.

5- Ref. POA MOTHER doc. 0037880

6- Creepage distance > 800 V

7- Creepage distance 250 V

8- Creepage distance as shown in the 664-1 CEI / IEC standard.





Figure 32. SO16N package dimensions



#### Package mechanical data

Dim.	mm				
Dini.	Min	Тур	Max		
А			1.75		
A1	0.1		0.25		
A2	1.25				
b	0.31		0.51		
С	0.17		0.25		
D	9.8	9.9	10		
E	5.8	6	6.2		
E1	3.8	3.9	4		
е		1.27			
h	0.25		0.5		
L	0.4		1.27		
k	0		8		
CCC			0.1		

Table 10	SO16N	mechanical	data
		meenamea	uala

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# 18 Revision history

Date	Revision	Changes			
21-Jan-2009	1	Initial release			
07-Dec-2009	2	Updated Figure 7 on page 11			
14-May-2010	3	Updated Figure 3 on page 5 and Table 3 on page 5			
26-Aug-2010	4	Updated Table 3 on page 5, Figure 16 on page 13 and Figure 21 on page 16			
10-Oct-2011	5	Updated Figure 32 on page 27 and Table 7 on page 8			
26-May-2014	6	<ul> <li>Updated the features in cover page, Table 3: Pin description, Table 4: Absolute maximum ratings, Table 6: Power section, Table 7: Supply section.</li> <li>Modified Figure 17, 18, 19 and 20.</li> <li>Added Section 16: Layout guidelines and design recommendations.</li> <li>Minor text changes.</li> </ul>			
13-Jun-2014	7	Updated <i>Table 3: Pin description</i> and <i>Table 6: Power section</i> . Minor text changes.			

Table 11.	Document	revision	history
	Document	10131011	III SLOI Y



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